



KERSEMI

PRODUCT SUMMARY		
V _{DS} (V)	200	
R _{DS(on)} (Ω)	V _{GS} = 10 V	0.18
Q _g (Max.) (nC)	70	
Q _{gs} (nC)	13	
Q _{gd} (nC)	39	
Configuration	Single	

FEATURES

- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- Isolated Central Mounting Hole
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Lead (Pb)-free Available

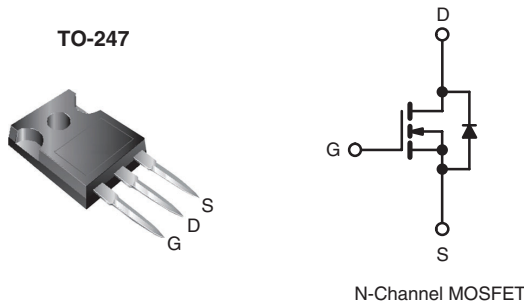


RoHS*
COMPLIANT

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-247 package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220 devices. The TO-247 is similar but superior to the earlier TO-218 package because its isolated mounting hole. It also provides greater creepage distances between pins to meet the requirements of most safety specifications.



ORDERING INFORMATION	
Package	TO-247
Lead (Pb)-free	IRFP240PbF
	SiHFP240-E3
SnPb	IRFP240
	SiHFP240

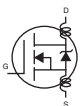

ABSOLUTE MAXIMUM RATINGS T _C = 25 °C, unless otherwise noted				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V _{DS}	200	V	
Gate-Source Voltage	V _{GS}	± 20		
Continuous Drain Current	V _{GS} at 10 V	T _C = 25 °C	A	
		T _C = 100 °C		
Pulsed Drain Current ^a	I _{DM}	80		
Linear Derating Factor		1.2	W/°C	
Single Pulse Avalanche Energy ^b	E _{AS}	510	mJ	
Repetitive Avalanche Current ^a	I _{AR}	20	A	
Repetitive Avalanche Energy ^a	E _{AR}	15	mJ	
Maximum Power Dissipation	T _C = 25 °C	P _D	150	W
Peak Diode Recovery dV/dt ^c		dV/dt	5.0	V/ns
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to + 150	°C	
Soldering Recommendations (Peak Temperature)	for 10 s	300 ^d		
Mounting Torque	6-32 or M3 screw		10	lbf · in
			1.1	N · m

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- V_{DD} = 50 V, starting T_J = 25 °C, L = 1.9 mH, R_G = 25 Ω, I_{AS} = 20 A (see fig. 12).
- I_{SD} ≤ 18 A, di/dt ≤ 150 A/μs, V_{DD} ≤ V_{DS}, T_J ≤ 150 °C.
- 1.6 mm from case.



THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	40	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.24	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.83	

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		200	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$		-	0.29	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$		-	-	25	μA
		$V_{DS} = 160\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 12\text{ A}^b$	-	-	0.18	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 12\text{ A}^b$		6.9	-	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$, see fig. 5		-	1300	-	pF
Output Capacitance	C_{oss}			-	400	-	
Reverse Transfer Capacitance	C_{rss}			-	130	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 18\text{ A}, V_{DS} = 160\text{ V}$, see fig. 6 and 13 ^b	-	-	70	nC
Gate-Source Charge	Q_{gs}			-	-	13	
Gate-Drain Charge	Q_{gd}			-	-	39	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 100\text{ V}, I_D = 18\text{ A}, R_G = 9.1\text{ }\Omega, R_D = 5.4\text{ }\Omega$, see fig. 10 ^b		-	14	-	ns
Rise Time	t_r			-	51	-	
Turn-Off Delay Time	$t_{d(off)}$			-	45	-	
Fall Time	t_f			-	36	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 		-	5.0	-	nH
Internal Source Inductance	L_S			-	13	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	20	A
Pulsed Diode Forward Current ^a	I_{SM}			-	-	80	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 20\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	2.0	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 18\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$		-	300	610	ns
Body Diode Reverse Recovery Charge	Q_{rr}			-	3.4	7.1	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.



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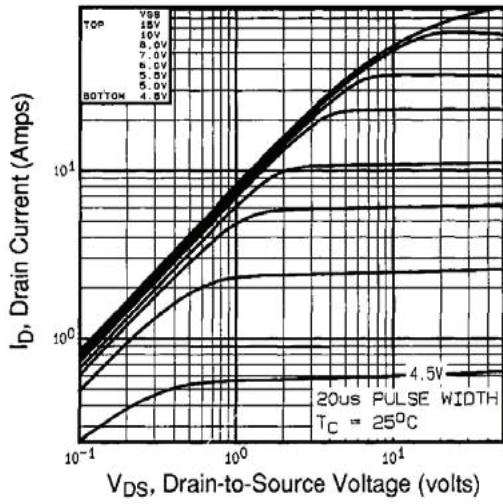


Fig. 1 - Typical Output Characteristics, $T_C = 25^\circ\text{C}$

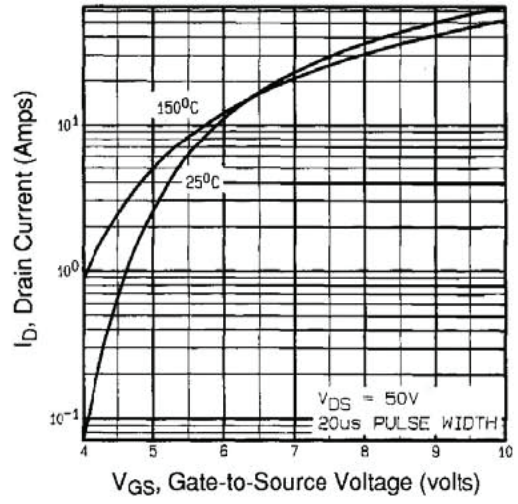


Fig. 3 - Typical Transfer Characteristics

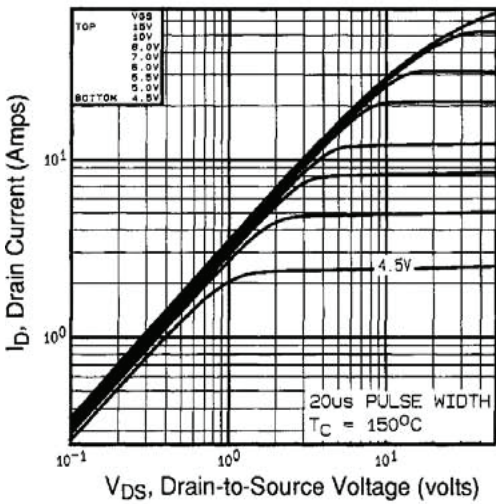


Fig. 2 - Typical Output Characteristics, $T_C = 150^\circ\text{C}$

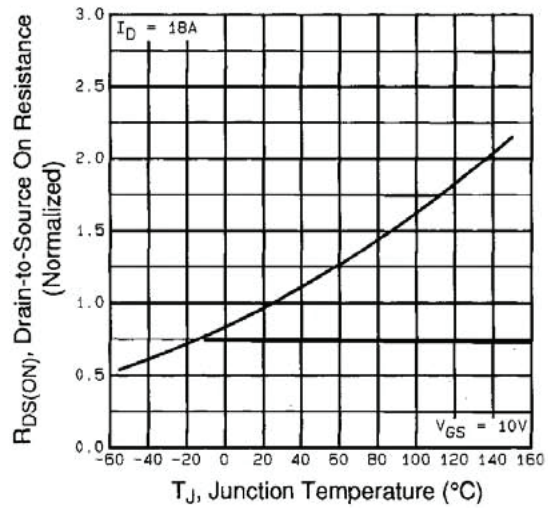


Fig. 4 - Normalized On-Resistance vs. Temperature

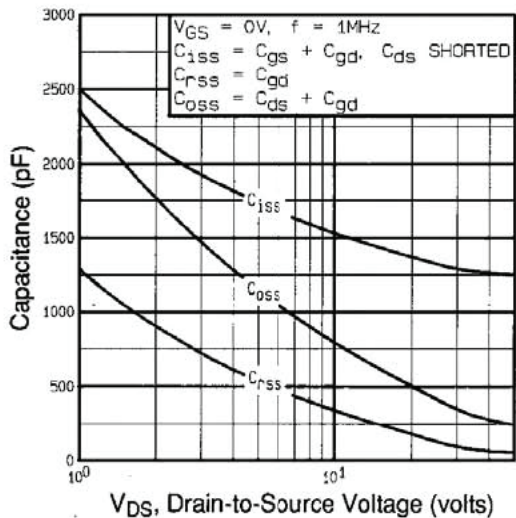


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

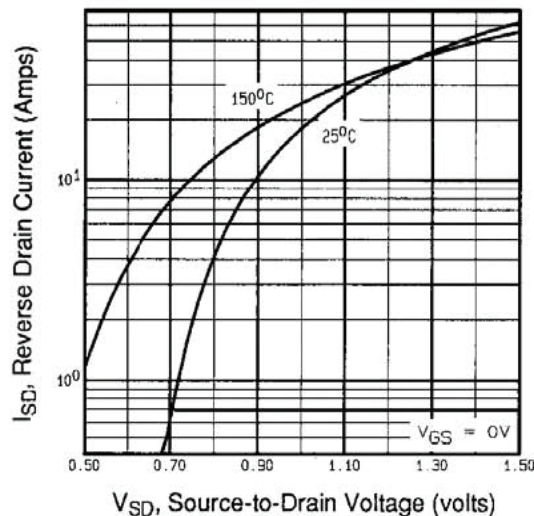


Fig. 7 - Typical Source-Drain Diode Forward Voltage

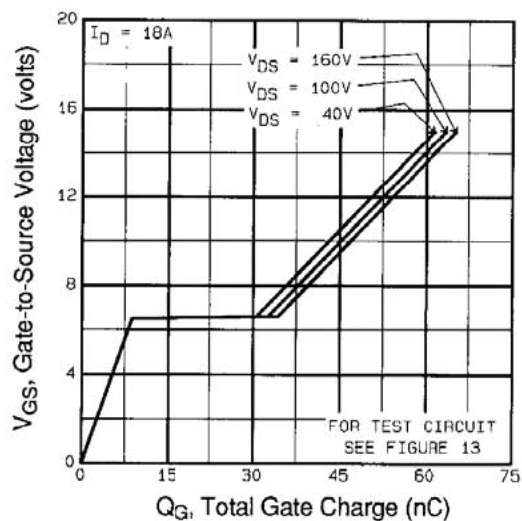


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

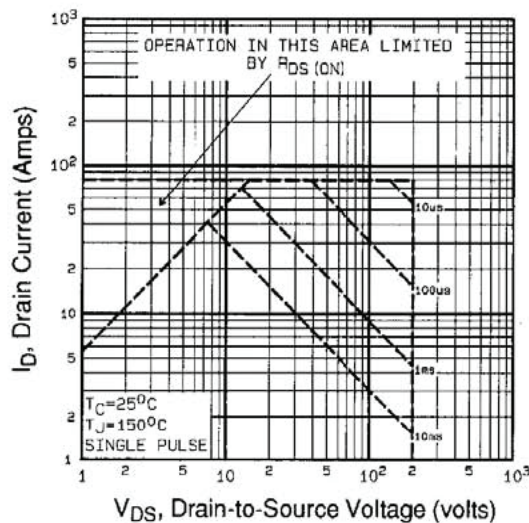


Fig. 8 - Maximum Safe Operating Area



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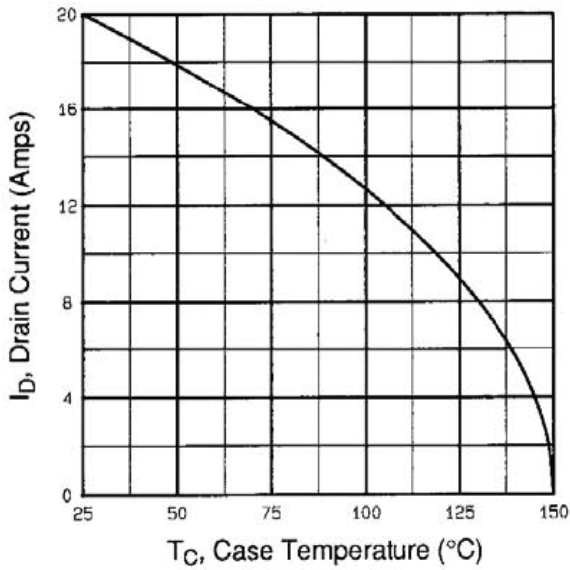


Fig. 9 - Maximum Drain Current vs. Case Temperature

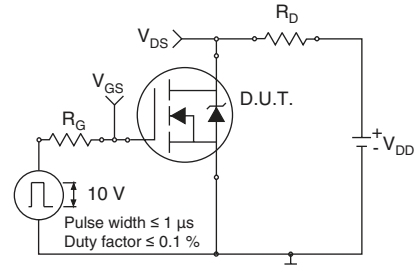


Fig. 10a - Switching Time Test Circuit

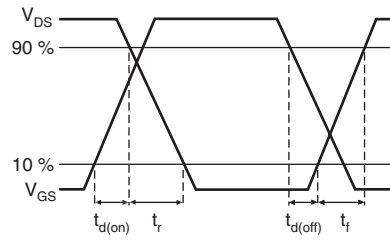


Fig. 10b - Switching Time Waveforms

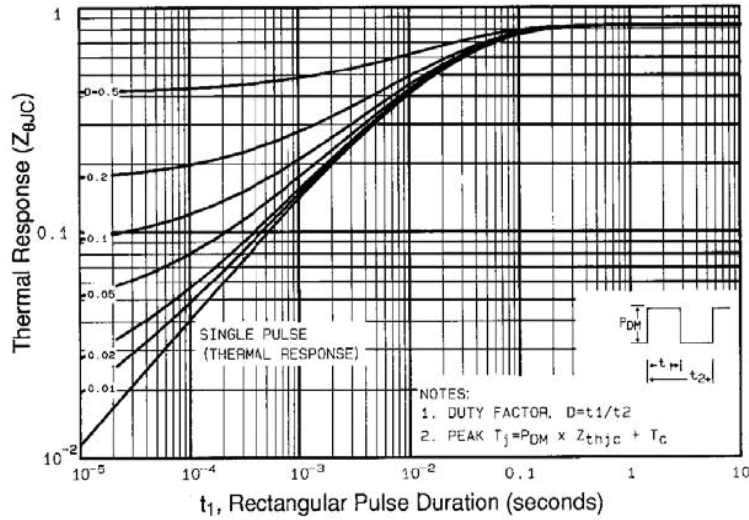


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

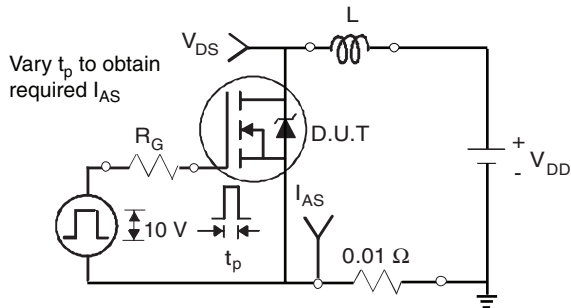


Fig. 12a - Unclamped Inductive Test Circuit

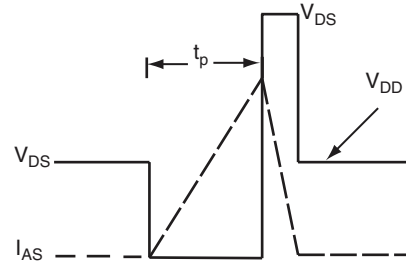


Fig. 12b - Unclamped Inductive Waveforms

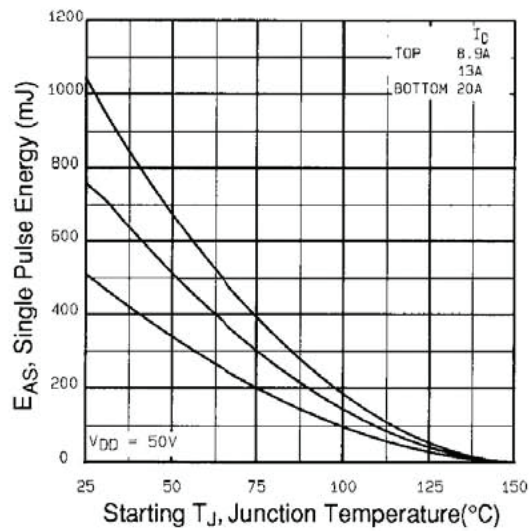


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

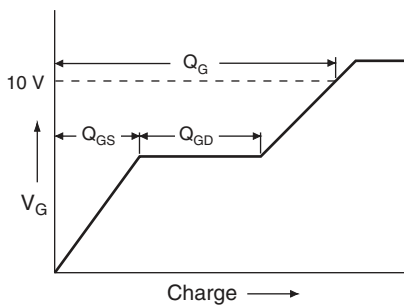


Fig. 13a - Basic Gate Charge Waveform

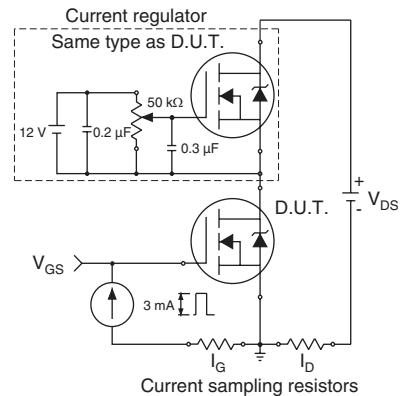
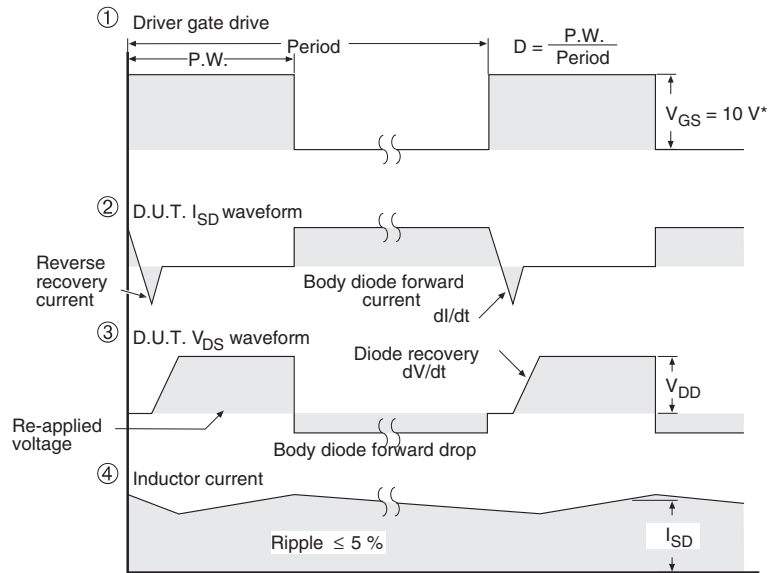
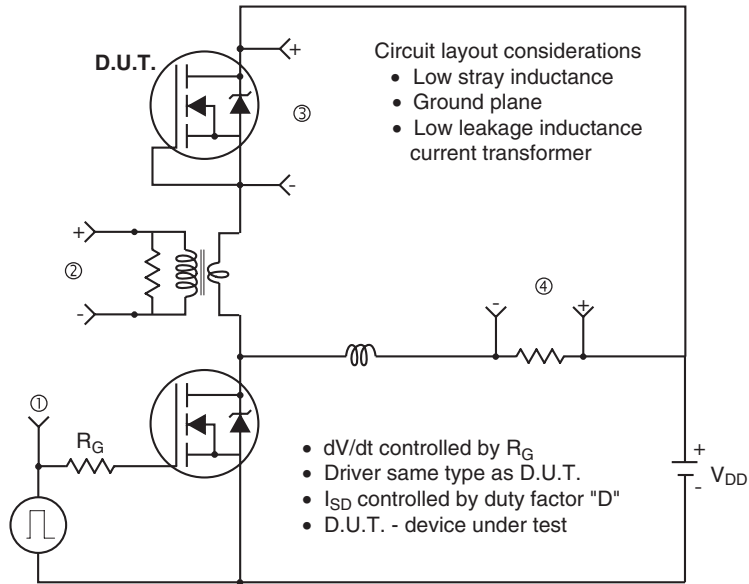


Fig. 13b - Gate Charge Test Circuit



Peak Diode Recovery dV/dt Test Circuit



* $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel